

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±10	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-200	mA
		T <sub>A</sub> = +70°C		-100	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-700	mA

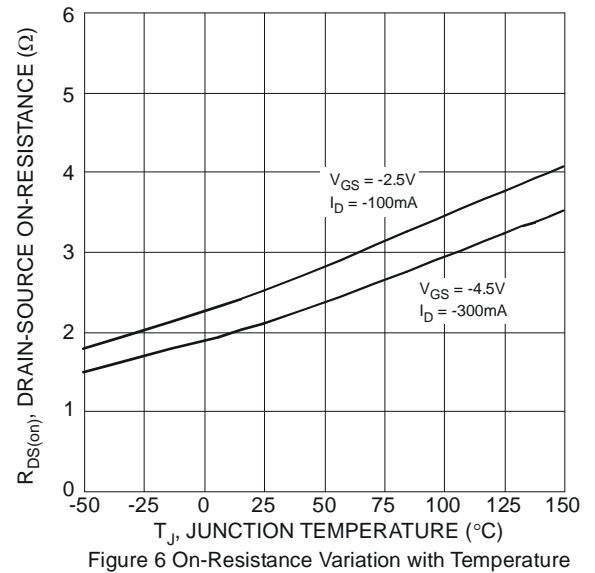
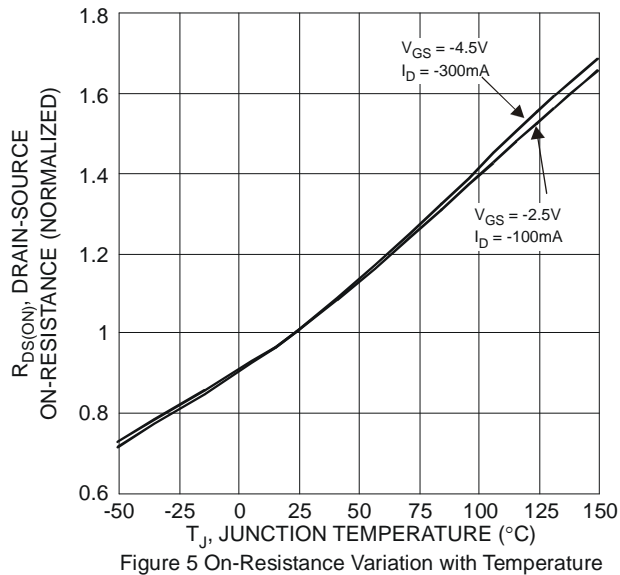
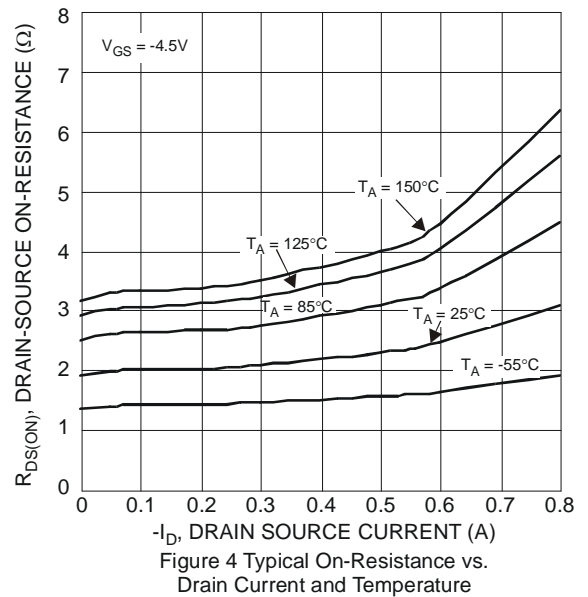
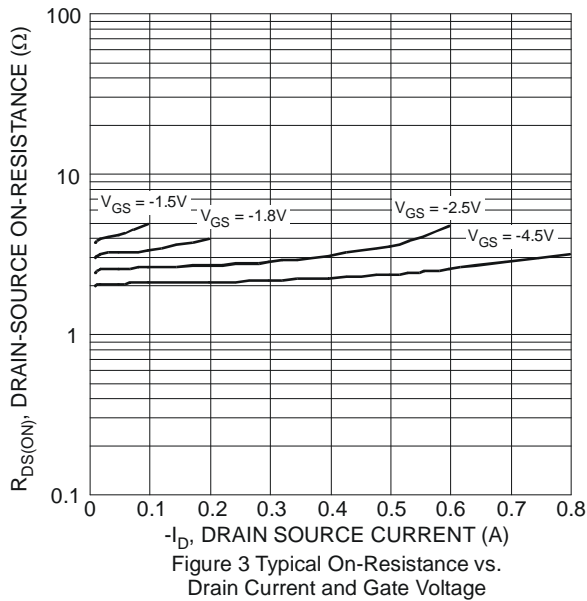
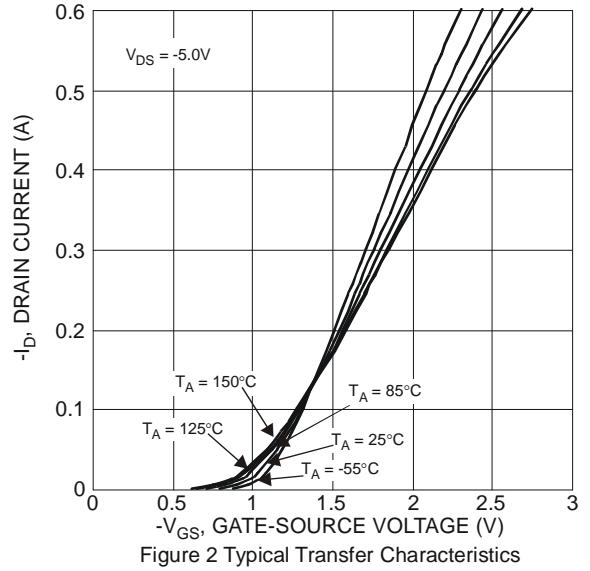
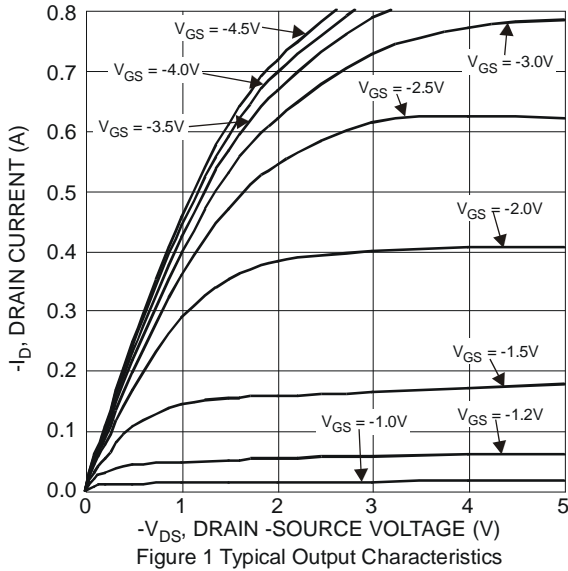
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P <sub>D</sub>	390	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	322	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current @ T <sub>C</sub> = +25°C	I <sub>DSS</sub>	—	—	-100	nA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.4	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	5	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -100mA
		—	—	6		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -50mA
		—	—	7		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -20mA
		—	—	10		V <sub>GS</sub> = -1.5V, I <sub>D</sub> = -10mA
		—	6	—		V <sub>GS</sub> = -1.2V, I <sub>D</sub> = -1mA
Diode Forward Voltage	V <sub>SD</sub>	—	-0.75	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -10mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	22.5	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	2.9	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.1	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	0.35	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -5V, I <sub>D</sub> = -200mA
Gate-Source Charge	Q <sub>gs</sub>	—	0.06	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.09	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.1	—	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -200mA
Turn-On Rise Time	t <sub>r</sub>	—	2.3	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	19.9	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	10.5	—	ns	

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  6. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.



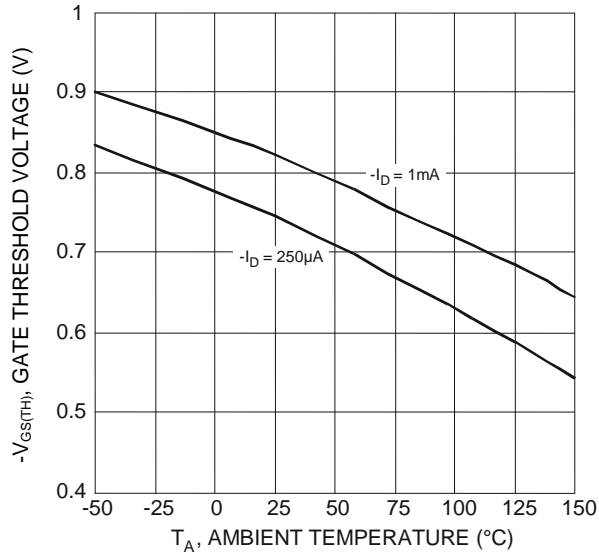


Figure 7 Gate Threshold Variation vs. Ambient Temperature

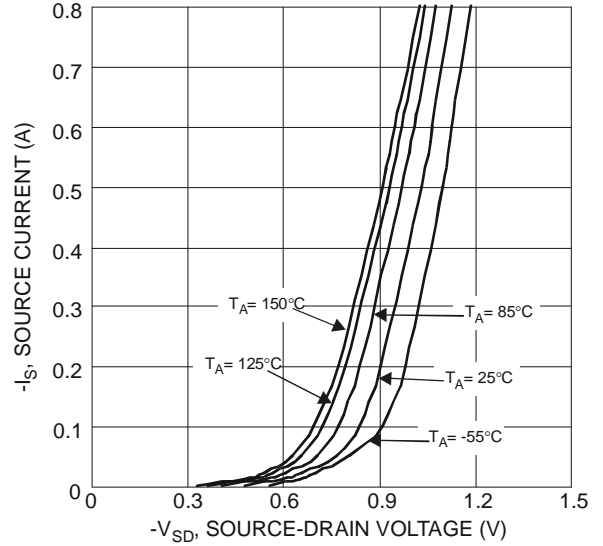


Figure 8 Diode Forward Voltage vs. Current

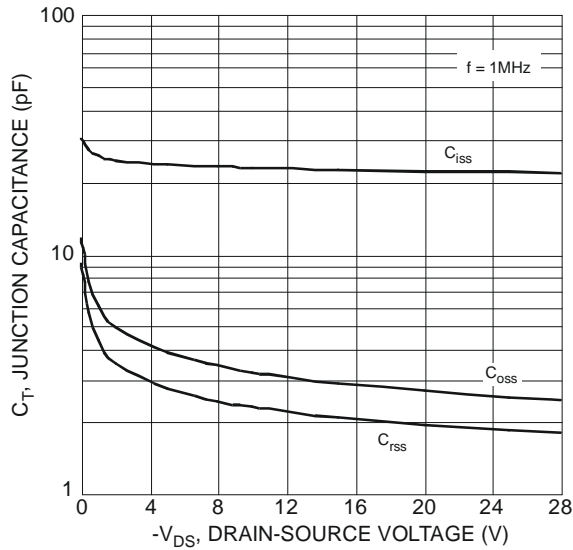


Figure 9 Typical Junction Capacitance

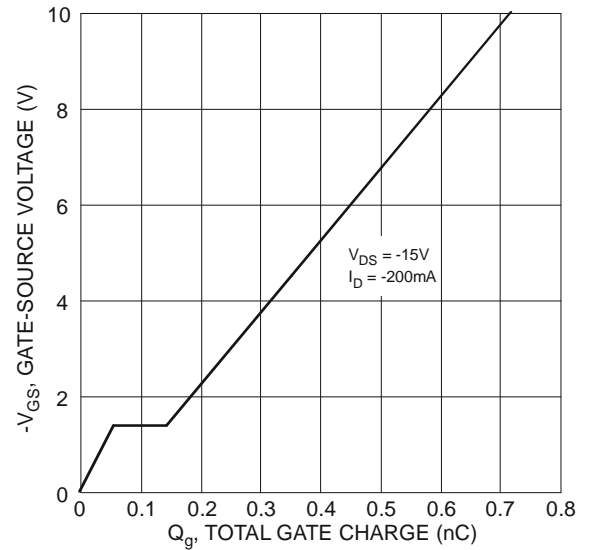


Figure 10 Gate-Charge Characteristics

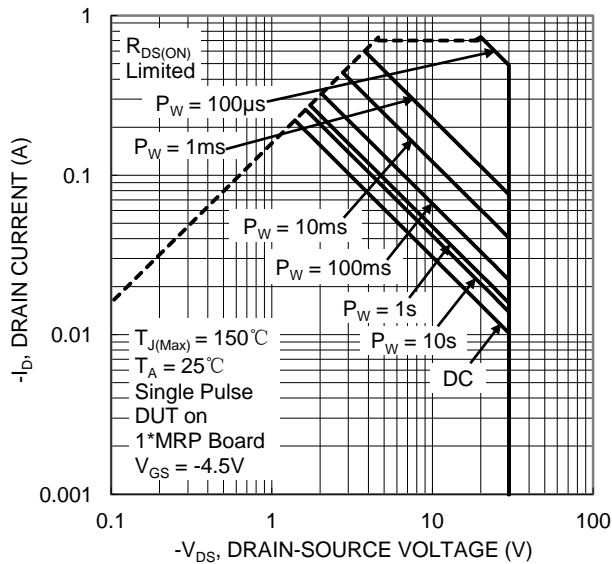
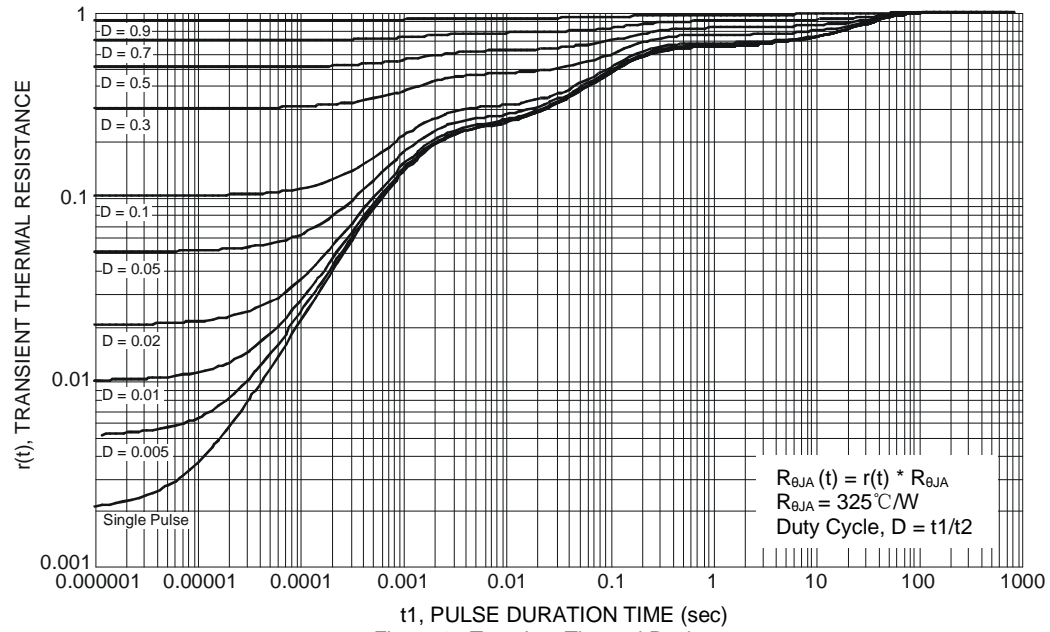


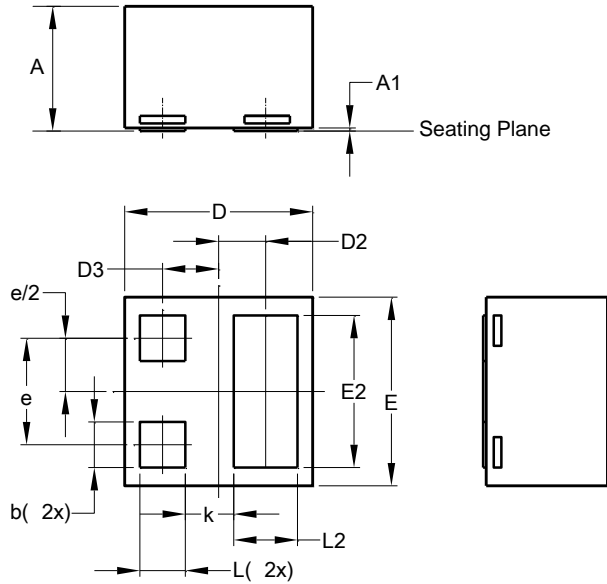
Figure 11 SOA, Safe Operation Area



## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### X2-DFN0606-3

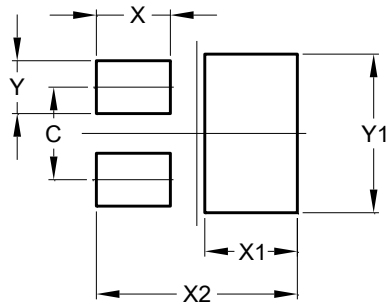


X2-DFN0606-3			
Dim	Min	Max	Typ
A	0.36	0.42	0.39
A1	0	0.05	0.02
b	0.10	0.20	0.15
D	0.57	0.67	0.62
D2	0.155 BSC		
D3	0.185 BSC		
E	0.57	0.67	0.62
E2	0.40	0.60	0.50
e	0.35 BSC		
k	0.16 REF		
L	0.09	0.21	0.15
L2	0.11	0.31	0.21
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### X2-DFN0606-3



Dimensions	Value (in mm)
C	0.350
X	0.280
X1	0.350
X2	0.760
Y	0.200
Y1	0.600

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